

<IGBT Modules>

CM600DX-24S1

HIGH POWER SWITCHING USE
INSULATED TYPE



dual switch (Half-Bridge)

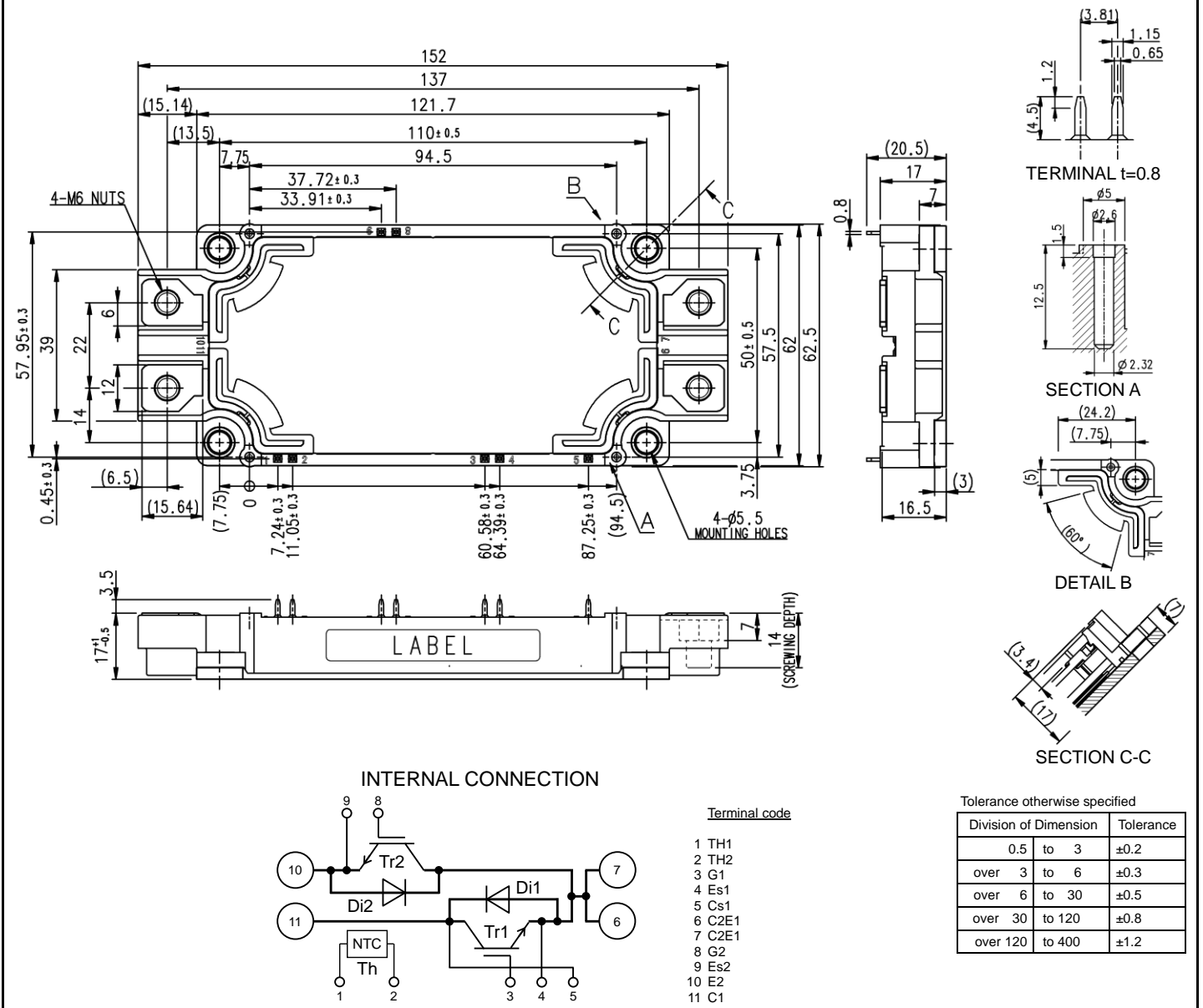
Collector current I_c 600 A
 Collector-emitter voltage V_{CES} 1200 V
 Maximum junction temperature T_{jmax} 175 °C

- Flat base Type
- Copper base plate (non-plating)
- Tin plating pin terminals
- RoHS Directive compliant
- UL Recognized under UL1557, File No. E323585

APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING & INTERNAL CONNECTION



CM600DX-24S1HIGH POWER SWITCHING USE
INSULATED TYPEMAXIMUM RATINGS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

INVERTER PART IGBT/FWD

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, $T_C=94\text{ }^\circ\text{C}$ (Note2, 4)	600	A
I_{CRM}		Pulse, Repetitive, $V_{GE}=15\text{ V}$ (Note3)	1200	
P_{tot}	Total power dissipation	$T_C=25\text{ }^\circ\text{C}$ (Note2, 4)	3330	W
I_E (Note1)	Emitter current	DC (Note2)	600	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	1200	

MODULE

Symbol	Item	Conditions	Rating	Unit
V_{isol}	Isolation voltage	Terminals to base plate, RMS, $f=60\text{ Hz}$, AC 1 min	4000	V
T_{jmax}	Maximum junction temperature	Instantaneous event (overload)	175	$^\circ\text{C}$
T_{Cmax}	Maximum case temperature	(Note4)	125	
T_{jop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	$^\circ\text{C}$
T_{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

INVERTER PART IGBT/FWD

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$, G-E short-circuited	-	-	1.0	mA	
I_{GES}	Gate-emitter leakage current	$V_{GE}=V_{GES}$, C-E short-circuited	-	-	0.5	μA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=60\text{ mA}$, $V_{CE}=10\text{ V}$	5.4	6.0	6.6	V	
V_{CESat} (Terminal)	Collector-emitter saturation voltage	$I_C=600\text{ A}$, $V_{GE}=15\text{ V}$, Refer to the figure of test circuit (Note5)	$T_j=25\text{ }^\circ\text{C}$	-	2.00	2.45	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.30	-	
			$T_j=150\text{ }^\circ\text{C}$	-	2.40	-	
V_{CESat} (Chip)		$I_C=600\text{ A}$, $V_{GE}=15\text{ V}$, (Note5)	$T_j=25\text{ }^\circ\text{C}$	-	1.85	2.35	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.10	-	
			$T_j=150\text{ }^\circ\text{C}$	-	2.15	-	
C_{ies}	Input capacitance	$V_{CE}=10\text{ V}$, G-E short-circuited	-	-	50	nF	
C_{oes}	Output capacitance		-	-	10		
C_{res}	Reverse transfer capacitance		-	-	0.83		
Q_G	Gate charge	$V_{CC}=600\text{ V}$, $I_C=600\text{ A}$, $V_{GE}=15\text{ V}$	-	1050	-	nC	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600\text{ V}$, $I_C=600\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, Inductive load	-	-	800	ns	
t_r	Rise time		-	-	200		
$t_{d(off)}$	Turn-off delay time		-	-	600		
t_f	Fall time		-	-	300		
V_{EC} (Note1) (Terminal)	Emitter-collector voltage	$I_E=600\text{ A}$, G-E short-circuited, Refer to the figure of test circuit (Note5)	$T_j=25\text{ }^\circ\text{C}$	-	2.8	3.60	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.4	-	
			$T_j=150\text{ }^\circ\text{C}$	-	2.3	-	
V_{EC} (Note1) (Chip)		$I_E=600\text{ A}$, G-E short-circuited, (Note5)	$T_j=25\text{ }^\circ\text{C}$	-	2.7	3.50	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.3	-	
			$T_j=150\text{ }^\circ\text{C}$	-	2.2	-	
t_{rr} (Note1)	Reverse recovery time	$V_{CC}=600\text{ V}$, $I_E=600\text{ A}$, $V_{GE}=\pm 15\text{ V}$,	-	-	300	ns	
Q_{rr} (Note1)	Reverse recovery charge	$R_G=0\text{ }\Omega$, Inductive load	-	16	-	μC	
E_{on}	Turn-on switching energy per pulse	$V_{CC}=600\text{ V}$, $I_C=I_E=600\text{ A}$,	-	91.5	-	mJ	
E_{off}	Turn-off switching energy per pulse	$V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, $T_j=150\text{ }^\circ\text{C}$,	-	63.1	-		
E_{rr} (Note1)	Reverse recovery energy per pulse	Inductive load	-	36.1	-	mJ	
$R_{CC'+EE'}$	Internal lead resistance	Main terminals-chip, per switch, $T_C=25\text{ }^\circ\text{C}$ (Note4)	-	-	0.4	m Ω	
r_g	Internal gate resistance	Per switch	-	5.0	-	Ω	

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HIGH POWER SWITCHING USE
INSULATED TYPE

ELECTRICAL CHARACTERISTICS (cont.; T_j=25 °C, unless otherwise specified)
NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R ₂₅	Zero-power resistance	T _C =25 °C (Note4)	4.85	5.00	5.15	kΩ
ΔR/R	Deviation of resistance	R ₁₀₀ =493 Ω, T _C =100 °C (Note4)	-7.3	-	+7.8	%
B _(25/50)	B-constant	Approximate by equation (Note6)	-	3375	-	K
P ₂₅	Power dissipation	T _C =25 °C (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R _{th(j-c)Q}	Thermal resistance	Junction to case, per Inverter IGBT (Note4)	-	-	45	K/kW
R _{th(j-c)D}		Junction to case, per Inverter FWD (Note4)	-	-	72	
R _{th(c-s)}	Contact thermal resistance	Case to heat sink, per 1 module, Thermal grease applied (Note4, 7)	-	15	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M _t	Mounting torque	Main terminals M 6 screw	3.5	4.0	4.5	N·m
M _s	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m
m	mass	-	-	350	-	g
d _s	Creepage distance	Terminal to terminal	17	-	-	mm
		Terminal to base plate	18.5	-	-	
d _a	Clearance	Terminal to terminal	10	-	-	mm
		Terminal to base plate	16.3	-	-	
e _c	Flatness of base plate	On the centerline X, Y (Note8)	±0	-	+100	μm

*. This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

- Junction temperature (T_j) should not increase beyond T_{jm ax} rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jm ax} rating.
- Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise.

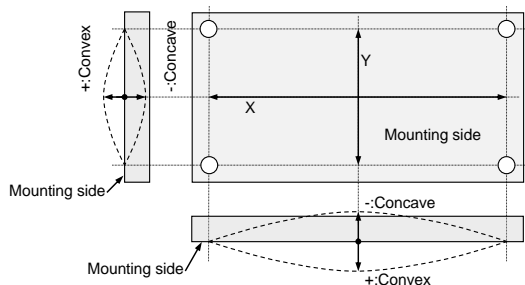
$$6. B(25/50) = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right)$$

R₂₅: resistance at absolute temperature T₂₅ [K], T₂₅=25 [°C] +273.15=298.15 [K]

R₅₀: resistance at absolute temperature T₅₀ [K], T₅₀=50 [°C] +273.15=323.15 [K]

7. Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K).

8. The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



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Note9 Use the following screws when mounting the printed circuit board (PCB) on the standoffs.

PCB thickness : t1.0~t1.6

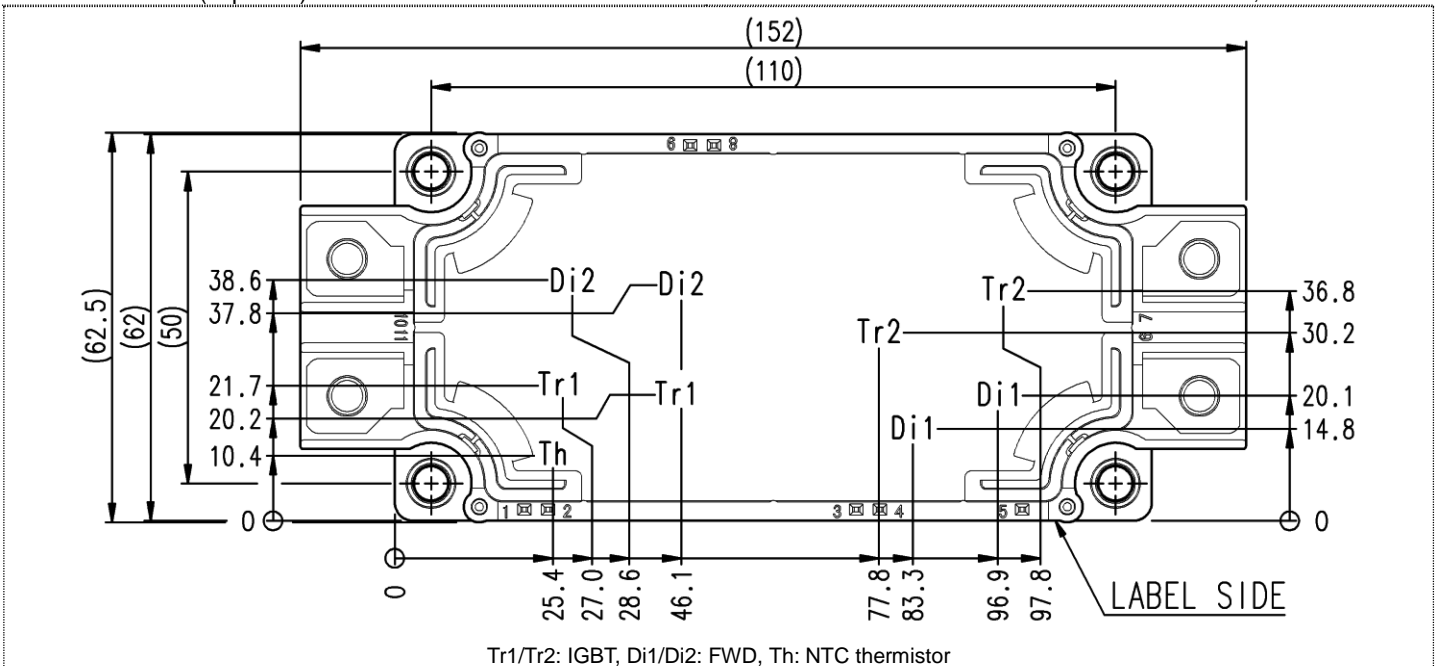
Type	Manufacturer	Size	Tightening torque (N·m)	Recommended tightening method
(1) PT®	EJOT	K25×8	0.55 ± 0.055	by handwork (equivalent to 30 r/min by mechanical screw driver) ~ 600 r/min (by mechanical screw driver)
(2) PT®		K25×10	0.75 ± 0.075	
(3) DELTA PT®		25×8	0.55 ± 0.055	
(4) DELTA PT®		25×10	0.75 ± 0.075	
(5) B1 tapping screw	-	φ2.6×10	0.75 ± 0.075	
		φ2.6×12		

RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{CC}	(DC) Supply voltage	Applied across C1-E2 terminals	-	600	850	V
V _{GEon}	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2 terminals	14.0	15.0	16.5	V
R _G	External gate resistance	Per switch	0	-	6.8	Ω

CHIP LOCATION (Top view)

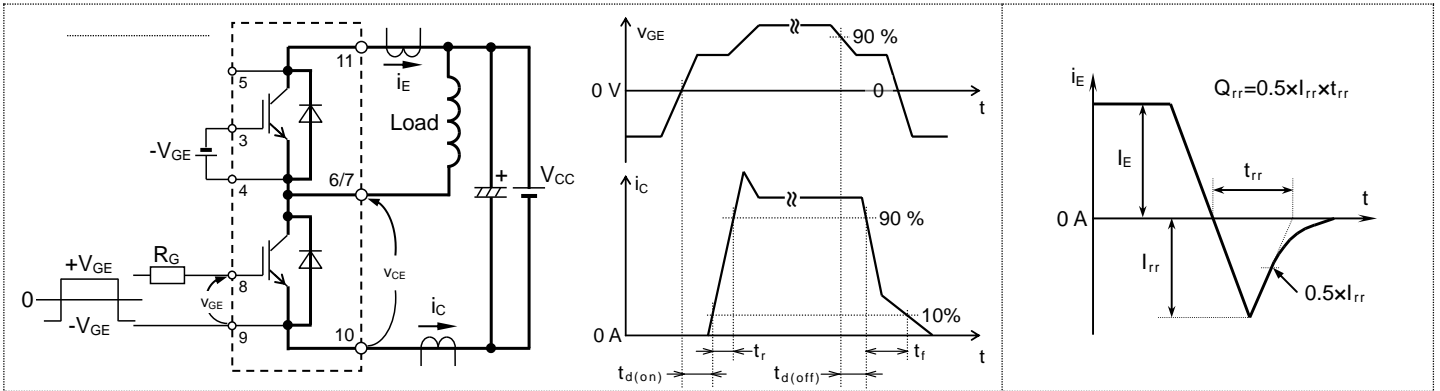
Dimension in mm, tolerance: ±1 mm



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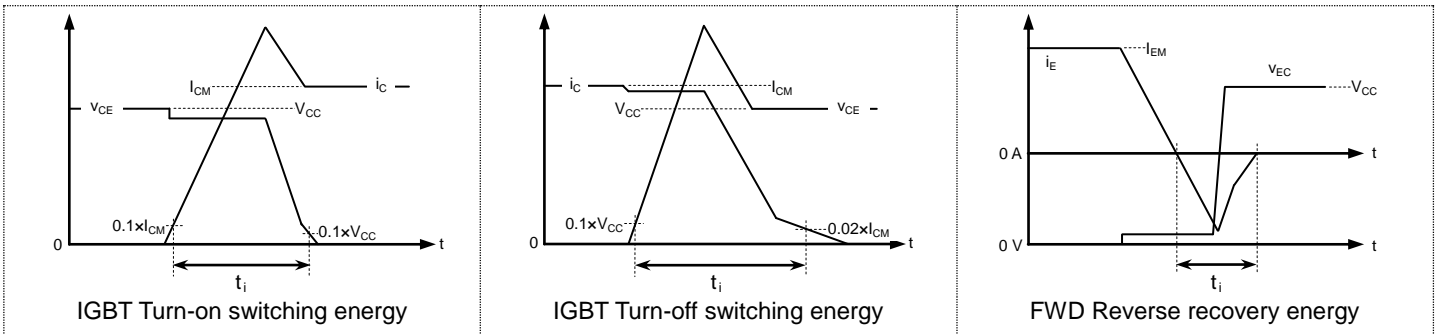
HIGH POWER SWITCHING USE
INSULATED TYPE

TEST CIRCUIT AND WAVEFORMS



Switching characteristics test circuit and waveforms

t_{rr} , Q_{rr} characteristics test waveform



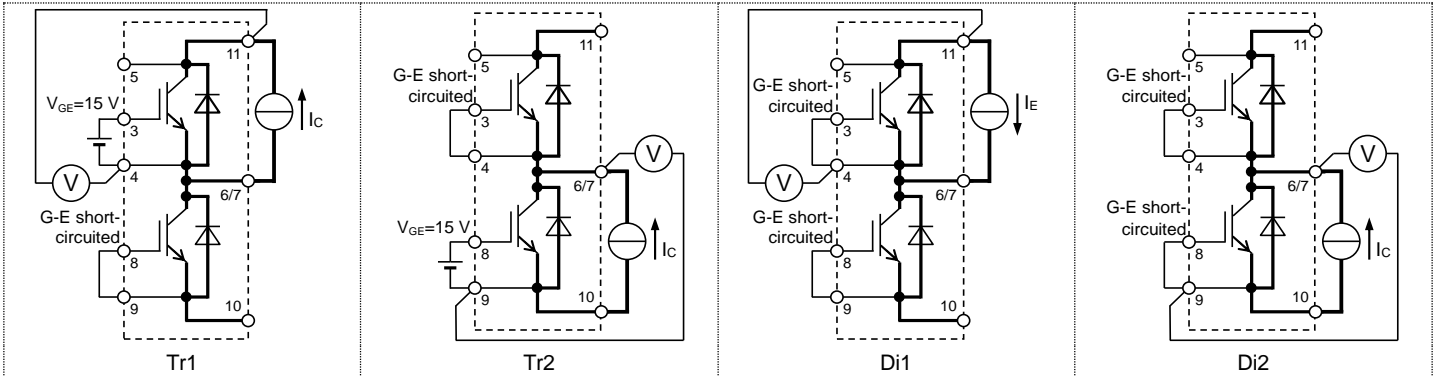
IGBT Turn-on switching energy

IGBT Turn-off switching energy

FWD Reverse recovery energy

Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT



V_{CEsat} characteristics test circuit

V_{EC} characteristics test circuit

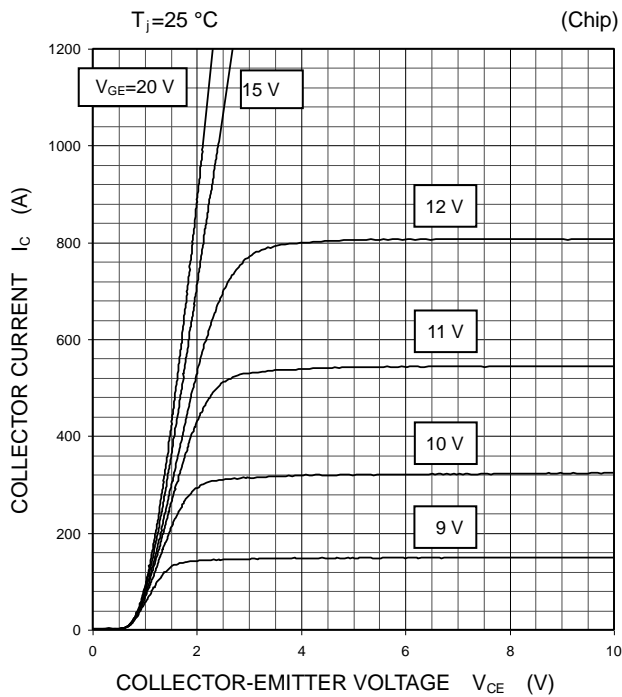
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HIGH POWER SWITCHING USE
INSULATED TYPE

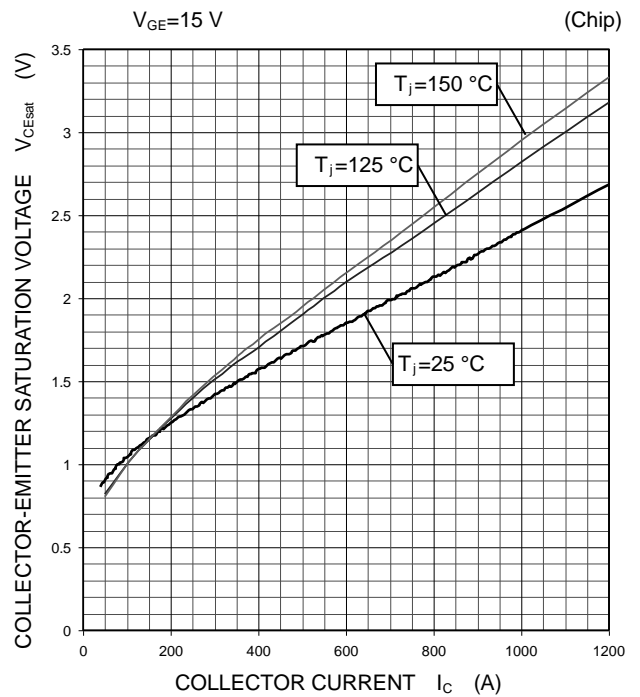
PERFORMANCE CURVES

INVERTER PART

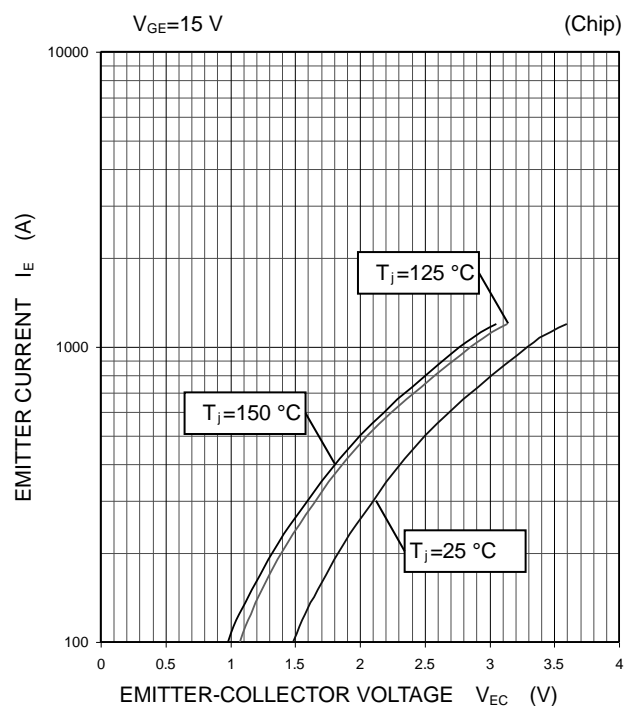
OUTPUT CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)



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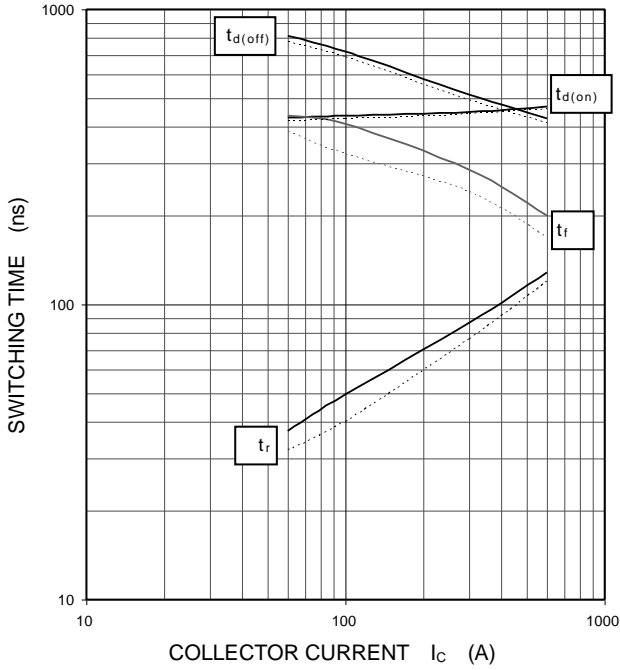
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

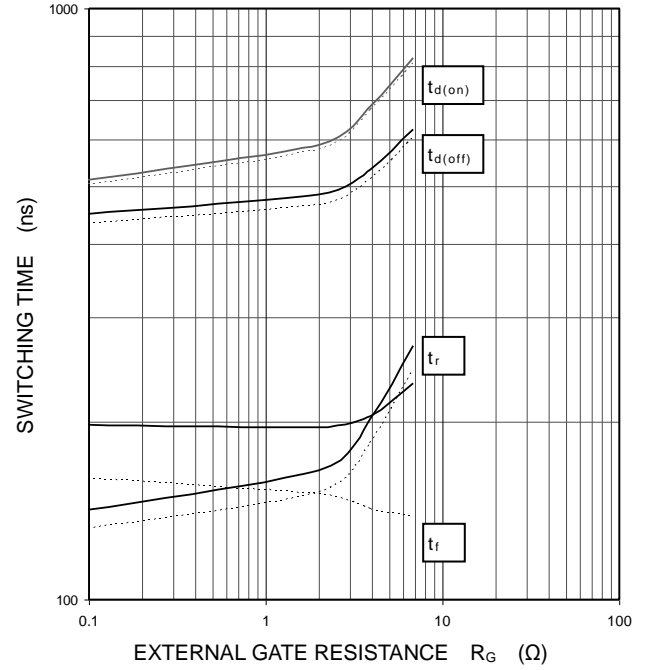
HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$, INDUCTIVE LOAD
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



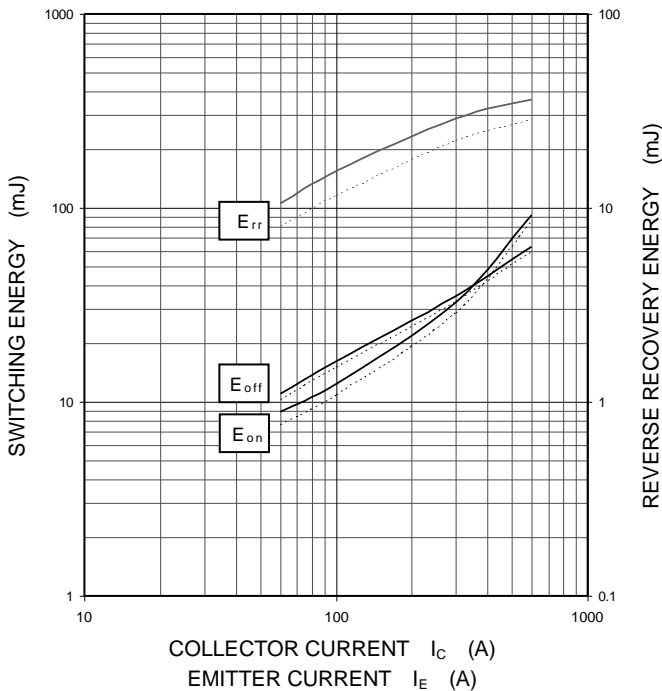
HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C=600\text{ A}$, INDUCTIVE LOAD
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



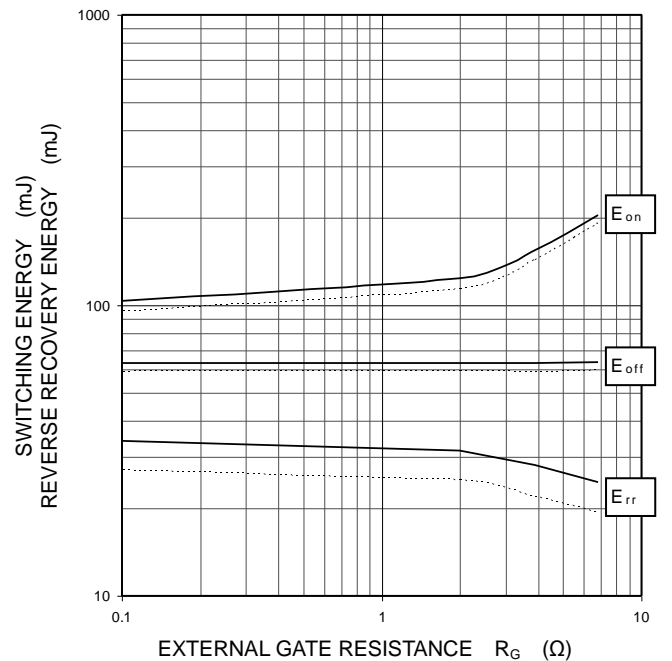
HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$,
INDUCTIVE LOAD, PER PULSE
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C/I_E=600\text{ A}$,
INDUCTIVE LOAD, PER PULSE
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



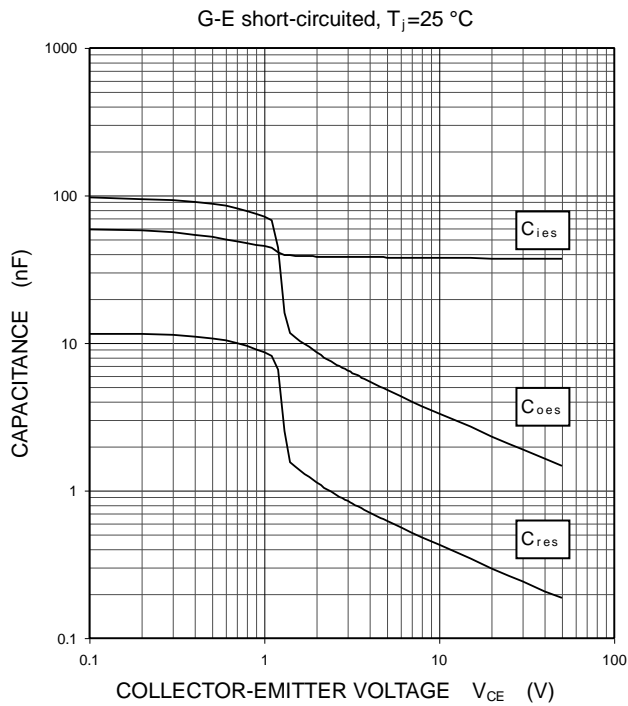
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HIGH POWER SWITCHING USE
INSULATED TYPE

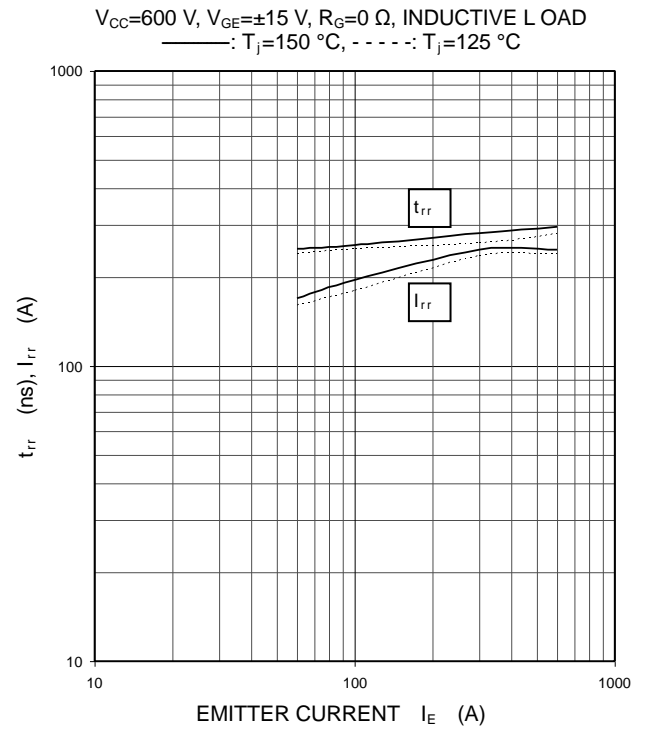
PERFORMANCE CURVES

INVERTER PART

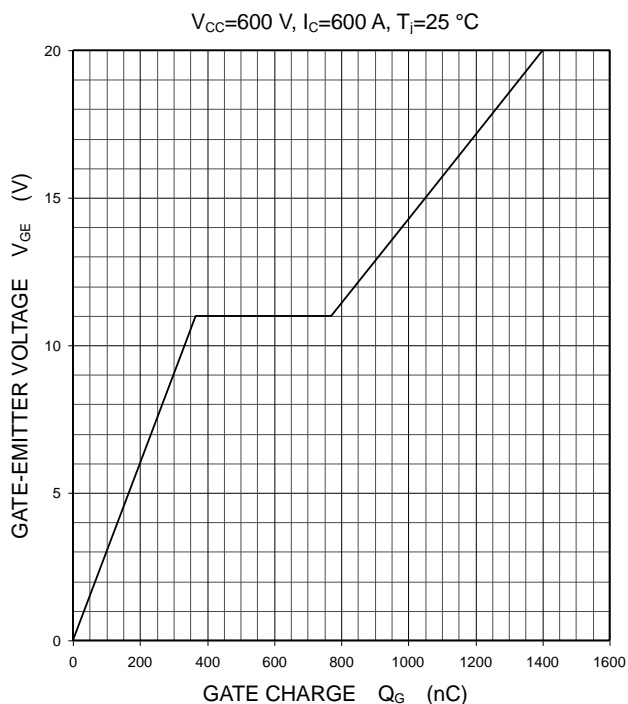
CAPACITANCE CHARACTERISTICS
(TYPICAL)



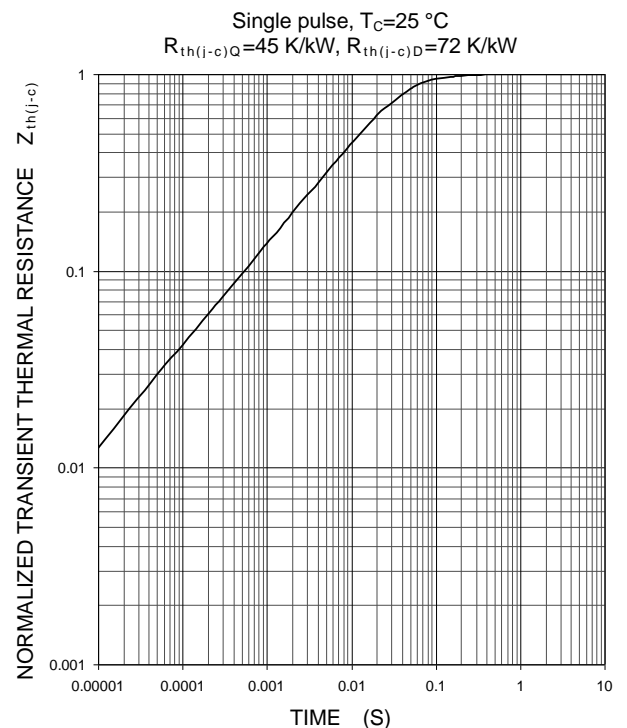
FREE WHEELING DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



GATE CHARGE CHARACTERISTICS
(TYPICAL)



TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS
(MAXIMUM)



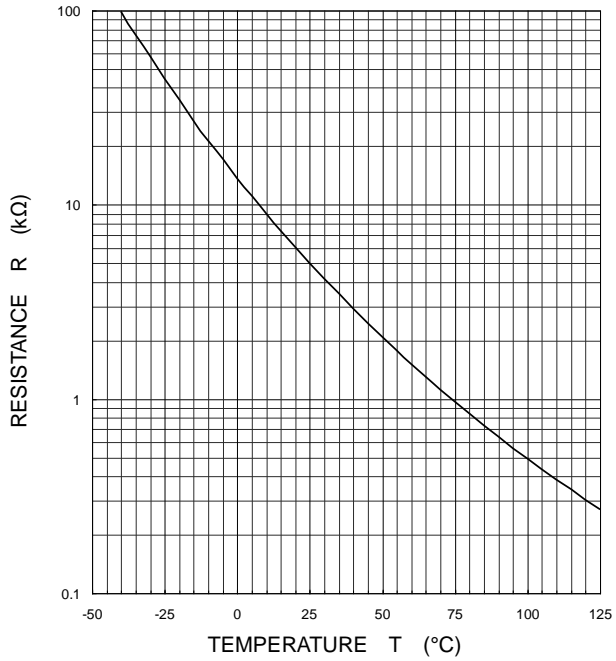
CM600DX-24S1

HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

NTC thermistor part

TEMPERATURE CHARACTERISTICS
(TYPICAL)



Keep safety first in your circuit designs!

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